# Kimberly A Dick

List of Publications by Year
in descending order



| | | | |
|---|---|---|---|
| 182 papers | 10,244 citations | 36303 51 h-index | 37204 96 g-index |
| 186 all docs | 186 docs citations | 186 times ranked | 7349 citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Direct Observations of Twin Formation Dynamics in Binary Semiconductors. ACS Nanoscience Au, 2022, 2, 49-56. | 4.8 | 8 |
| 2 | Post-nucleation evolution of the liquidâ€“solid interface in nanowire growth. Nanotechnology, 2022, 33, 105607. | 2.6 | 3 |
| 3 | Experimental Verification of the Work Fluctuation-Dissipation Relation for Information-to-Work Conversion. Physical Review Letters, 2022, 128, 040602. | 7.8 | 12 |
| 4 | Simulating Vaporâ€“Liquidâ€“Solid Growth of Au-Seeded InGaAs Nanowires. ACS Nanoscience Au, 2022, 2, 239-249. | 4.8 | 7 |
| 5 | Growth selectivity control of InAs shells on crystal phase engineered GaAs nanowires. Nanoscale Advances, 2022, 4, 3330-3341. | 4.6 | 5 |
| 6 | Time-resolved photoluminescence studies of single interface wurtzite/zincblende heterostructured InP nanowires. Applied Physics Letters, 2022, 120, . | 3.3 | 2 |
| 7 | Interface Dynamics in Agâ€“Cu<sub>3</sub>P Nanoparticle Heterostructures. Journal of the American Chemical Society, 2022, 144, 248-258. | 13.7 | 10 |
| 8 | Effects of Parity and Symmetry on the Aharonovâ€“Bohm Phase of a Quantum Ring. Nano Letters, 2022, 22, 334-339. | 9.1 | 5 |
| 9 | Enabling <i>In Situ</i> Studies of Metal-Organic Chemical Vapor Deposition in a Transmission Electron Microscope. Microscopy and Microanalysis, 2022, 28, 1484-1492. | 0.4 | 11 |
| 10 | Unraveling the Ultrafast Hot Electron Dynamics in Semiconductor Nanowires. ACS Nano, 2021, 15, 1133-1144. | 14.6 | 18 |
| 11 | Vaporâ€“solidâ€“solid growth dynamics in GaAs nanowires. Nanoscale Advances, 2021, 3, 5928-5940. | 4.6 | 16 |
| 12 | Gate control, g factors, and spin-orbit energy of p -type GaSb nanowire quantum dot devices. Physical Review B, 2021, 103, . | 3.2 | 1 |
| 13 | Symmetry-controlled singlet-triplet transition in a double-barrier quantum ring. Physical Review B, 2021, 104, . | 3.2 | 4 |
| 14 | Efficient and continuous microwave photoconversion in hybrid cavity-semiconductor nanowire double quantum dot diodes. Nature Communications, 2021, 12, 5130. | 12.8 | 17 |
| 15 | Compositional Correlation between the Nanoparticle and the Growing Au-Assisted In<sub><i>x</i></sub>Ga<sub>1â€“<i>x</i></sub>As Nanowire. Journal of Physical Chemistry Letters, 2021, 12, 7590-7595. | 4.6 | 12 |
| 16 | Unraveling electronic band structure of narrow-bandgap pâ€“n nanojunctions in heterostructured nanowires. Physical Chemistry Chemical Physics, 2021, 23, 25019-25023. | 2.8 | 6 |
| 17 | Self-selective formation of ordered 1D and 2D GaBi structures on wurtzite GaAs nanowire surfaces. Nature Communications, 2021, 12, 5990. | 12.8 | 3 |
| 18 | Measuring Surface Tension of III-V Nanowire Au-Catalyst Droplets with an E-field. Microscopy and Microanalysis, 2021, 27, 27-28. | 0.4 | 0 |

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| 19 | Atomically sharp, crystal phase defined GaAs quantum dots. Applied Physics Letters, 2021, 119, . | 3.3 | 7 |
| 20 | Two-dimensional electron gas at wurtziteâ€“zinc-blende InP interfaces induced by modulation doping. Applied Physics Letters, 2020, 116, 232103. | 3.3 | 9 |
| 21 | Limits of IIIâ€“V Nanowire Growth Based on Droplet Dynamics. Journal of Physical Chemistry Letters, 2020, 11, 2949-2954. | 4.6 | 14 |
| 22 | Magnetic-Field-Independent Subgap States in Hybrid Rashba Nanowires. Physical Review Letters, 2020, 125, 017701. | 7.8 | 38 |
| 23 | Effect of Radius on Crystal Structure Selection in IIIâ€“V Nanowire Growth. Crystal Growth and Design, 2020, 20, 5373-5379. | 3.0 | 7 |
| 24 | In situ metal-organic chemical vapour deposition growth of IIIâ€“V semiconductor nanowires in the Lund environmental transmission electron microscope. Semiconductor Science and Technology, 2020, 35, 034004. | 2.0 | 20 |
| 25 | Independent Control of Nucleation and Layer Growth in Nanowires. ACS Nano, 2020, 14, 3868-3875. | 14.6 | 31 |
| 26 | Selective tuning of spin-orbital Kondo contributions in parallel-coupled quantum dots. Physical Review B, 2020, 101, . | 3.2 | 2 |
| 27 | Non-resonant Raman scattering of wurtzite GaAs and InP nanowires. Optics Express, 2020, 28, 11016. | 3.4 | 1 |
| 28 | Spectroscopy of the superconducting proximity effect in nanowires using integrated quantum dots. Communications Physics, 2019, 2, . | 5.3 | 28 |
| 29 | In situ analysis of catalyst composition during gold catalyzed GaAs nanowire growth. Nature Communications, 2019, 10, 4577. | 12.8 | 49 |
| 30 | Kinetics of Auâ€“Ga Droplet Mediated Decomposition of GaAs Nanowires. Nano Letters, 2019, 19, 3498-3504. | 9.1 | 18 |
| 31 | Simultaneous Growth of Pure Wurtzite and Zinc Blende Nanowires. Nano Letters, 2019, 19, 2723-2730. | 9.1 | 13 |
| 32 | Nanowire morphology and particle phase control by tuning the In concentration of the foreign metal nanoparticle. Nanotechnology, 2019, 30, 054005. | 2.6 | 4 |
| 33 | Simulation of GaAs Nanowire Growth and Crystal Structure. Nano Letters, 2019, 19, 1197-1203. | 9.1 | 27 |
| 34 | Sb Incorporation in Wurtzite and Zinc Blende InAs<sub>1âˆ’</sub><i><sub>x</sub></i>Sb<i><sub>x</sub></i> Branches on InAs Template Nanowires. Small, 2018, 14, e1703785. | 10.0 | 5 |
| 35 | Hydrogen-assisted spark discharge generated metal nanoparticles to prevent oxide formation. Aerosol Science and Technology, 2018, 52, 347-358. | 3.1 | 31 |
| 36 | Temperature dependent electronic band structure of wurtzite GaAs nanowires. Nanoscale, 2018, 10, 1481-1486. | 5.6 | 16 |

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| 37 | Spatial Control of Multiphoton Electron Excitations in InAs Nanowires by Varying Crystal Phase and Light Polarization. Nano Letters, 2018, 18, 907-915. | 9.1 | 11 |
| 38 | Atomic-Resolution Spectrum Imaging of Semiconductor Nanowires. Nano Letters, 2018, 18, 1557-1563. | 9.1 | 21 |
| 39 | Spectroscopy and level detuning of few-electron spin states in parallel InAs quantum dots. Physical Review B, 2018, 98, . | 3.2 | 6 |
| 40 | Understanding GaAs Nanowire Growth in the Agâ€“Au Seed Materials System. Crystal Growth and Design, 2018, 18, 6702-6712. | 3.0 | 5 |
| 41 | Branched InAs nanowire growth by droplet confinement. Applied Physics Letters, 2018, 113, 123104. | 3.3 | 11 |
| 42 | Tuning the Two-Electron Hybridization and Spin States in Parallel-Coupled InAs Quantum Dots. Physical Review Letters, 2018, 121, 156802. | 7.8 | 14 |
| 43 | Realization of Wurtzite GaSb Using InAs Nanowire Templates. Advanced Functional Materials, 2018, 28, 1800512. | 14.9 | 13 |
| 44 | Radial band bending at wurtziteâ€“zinc-blendeâ€“GaAs interfaces. Nano Futures, 2018, 2, 035002. | 2.2 | 7 |
| 45 | Kinetic Engineering of Wurtzite and Zinc-Blende AlSb Shells on InAs Nanowires. Nano Letters, 2018, 18, 5775-5781. | 9.1 | 6 |
| 46 | Polarity and growth directions in Sn-seeded GaSb nanowires. Nanoscale, 2017, 9, 3159-3168. | 5.6 | 24 |
| 47 | Annealing of Au, Ag and Auâ€“Ag alloy nanoparticle arrays on GaAs (100) and (111)B. Nanotechnology, 2017, 28, 205702. | 2.6 | 11 |
| 48 | Crystal Structure Induced Preferential Surface Alloying of Sb on Wurtzite/Zinc Blende GaAs Nanowires. Nano Letters, 2017, 17, 3634-3640. | 9.1 | 14 |
| 49 | Direct nucleation, morphology and compositional tuning of InAs<sub>1âˆ’<i>x</i></sub>Sb<i><sub>x</sub></i>nanowires on InAs (111) B substrates. Nanotechnology, 2017, 28, 165601. | 2.6 | 23 |
| 50 | Conduction Band Offset and Polarization Effects in InAs Nanowire Polytype Junctions. Nano Letters, 2017, 17, 902-908. | 9.1 | 34 |
| 51 | Electronic Structure Changes Due to Crystal Phase Switching at the Atomic Scale Limit. ACS Nano, 2017, 11, 10519-10528. | 14.6 | 15 |
| 52 | Thermodynamic Stability of Gold-Assisted InAs Nanowire Growth. Journal of Physical Chemistry C, 2017, 121, 21678-21684. | 3.1 | 11 |
| 53 | Imaging Atomic Scale Dynamics on IIIâ€“V Nanowire Surfaces During Electrical Operation. Scientific Reports, 2017, 7, 12790. | 3.3 | 5 |
| 54 | Parallel-Coupled Quantum Dots in InAs Nanowires. Nano Letters, 2017, 17, 7847-7852. | 9.1 | 27 |

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| 55 | Micro-Raman spectroscopy for the detection of stacking fault density in InAs and GaAs nanowires. Physical Review B, 2017, 96, . | 3.2 | 6 |
| 56 | Characterization of individual stacking faults in aÂwurtzite GaAs nanowire by nanobeam X-ray diffraction. Journal of Synchrotron Radiation, 2017, 24, 981-990. | 2.4 | 9 |
| 57 | Demonstration of Sn-seeded GaSb homo- and GaAsâ€“GaSb heterostructural nanowires. Nanotechnology, 2016, 27, 175602. | 2.6 | 11 |
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| 64 | InAs nanowire GAA n-MOSFETs with 12â€“15 nm diameter. , 2016, , . |  | 14 |
| 65 | Schottky barrier and contact resistance of InSb nanowire field-effect transistors. Nanotechnology, 2016, 27, 275204. | 2.6 | 14 |
| 66 | Can antimonide-based nanowires form wurtzite crystal structure?. Nanoscale, 2016, 8, 2778-2786. | 5.6 | 20 |
| 67 | Interface dynamics and crystal phase switching in GaAs nanowires. Nature, 2016, 531, 317-322. | 27.8 | 272 |
| 68 | Wurtzite GaAs Quantum Wires: One-Dimensional Subband Formation. Nano Letters, 2016, 16, 2774-2780. | 9.1 | 23 |
| 69 | Silver as Seed-Particle Material for GaAs Nanowiresâ€"Dictating Crystal Phase and Growth Direction by Substrate Orientation. Nano Letters, 2016, 16, 2181-2188. | 9.1 | 33 |
| 70 | Polytype Attainability in IIIâ€“V Semiconductor Nanowires. Crystal Growth and Design, 2016, 16, 371-379. | 3.0 | 23 |
| 71 | Phase Transformation in Radially Merged Wurtzite GaAs Nanowires. Crystal Growth and Design, 2015, 15, 4795-4803. | 3.0 | 27 |
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| 73 | Selective GaSb radial growth on crystal phase engineered InAs nanowires. Nanoscale, 2015, 7, 10472-10481. | 5.6 | 42 |
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| 77 | Scanning Tunneling Spectroscopy on InAsâ€“GaSb Esaki Diode Nanowire Devices during Operation. Nano Letters, 2015, 15, 3684-3691. | 9.1 | 16 |
| 78 | Atomic Scale Surface Structure and Morphology of InAs Nanowire Crystal Superlattices: The Effect of Epitaxial Overgrowth. ACS Applied Materials & Interfaces, 2015, 7, 5748-5755. | 8.0 | 23 |
| 79 | Crystal phase control in GaAs nanowires: opposing trends in the Ga- and As-limited growth regimes. Nanotechnology, 2015, 26, 301001. | 2.6 | 43 |
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| 81 | Atomic-Scale Variability and Control of III-V Nanowire Growth Kinetics. Science, 2014, 343, 281-284. | 12.6 | 87 |
| 82 | Observation of type-II recombination in single wurtzite/zinc-blende GaAs heterojunction nanowires. Physical Review B, 2014, 89, . | 3.2 | 60 |
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| 88 | Crystal structure tuning in GaAs nanowires using HCl. Nanoscale, 2014, 6, 8257. | 5.6 | 9 |
| 89 | Crystal Phase-Dependent Nanophotonic Resonances in InAs Nanowire Arrays. Nano Letters, 2014, 14, 5650-5655. | 9.1 | 26 |
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| 91 | Electrical properties of GaSb/InAsSb core/shell nanowires. Nanotechnology, 2014, 25, 425201. | 2.6 | 32 |
| 92 | High resolution scanning gate microscopy measurements on InAs/GaSb nanowire Esaki diode devices. Nano Research, 2014, 7, 877-887. | 10.4 | 15 |
| 93 | Time-Resolved X-ray Diffraction Investigation of the Modified Phonon Dispersion in InSb Nanowires. Nano Letters, 2014, 14, 541-546. | 9.1 | 16 |
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| 95 | A General Approach for Sharp Crystal Phase Switching in InAs, GaAs, InP, and GaP Nanowires Using Only Group V Flow. Nano Letters, 2013, 13, 4099-4105. | 9.1 | 156 |
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| 97 | Large Thermoelectric Power Factor Enhancement Observed in InAs Nanowires. Nano Letters, 2013, 13, 4080-4086. | 9.1 | 107 |
| 98 | Conductance Enhancement of InAs/InP Heterostructure Nanowires by Surface Functionalization with Oligo(phenylene vinylene)s. ACS Nano, 2013, 7, 4111-4118. | 14.6 | 16 |
| 99 | High-Current GaSb/InAs(Sb) Nanowire Tunnel Field-Effect Transistors. IEEE Electron Device Letters, 2013, 34, 211-213. | 3.9 | 108 |
| 100 | Strategies To Control Morphology in Hybrid Group IIIâ€“V/Group IV Heterostructure Nanowires. Nano Letters, 2013, 13, 903-908. | 9.1 | 63 |
| 101 | Cu particle seeded InPâ€“InAs axial nanowire heterostructures. Physica Status Solidi - Rapid Research Letters, 2013, 7, 850-854. | 2.4 | 5 |
| 102 | Diameter Limitation in Growth of III-Sb-Containing Nanowire Heterostructures. ACS Nano, 2013, 7, 3668-3675. | 14.6 | 45 |
| 103 | Control of composition and morphology in InGaAs nanowires grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2013, 383, 158-165. | 1.5 | 39 |
| 104 | Self-catalyzed MBE grown GaAs/GaAs<sub><i>x</i></sub>Sb<sub>1âˆ’<i>x</i></sub>coreâ€“shell nanowires in ZB and WZ crystal structures. Nanotechnology, 2013, 24, 405601. | 2.6 | 21 |
| 105 | Control and understanding of kink formation in InAsâ€“InP heterostructure nanowires. Nanotechnology, 2013, 24, 345601. | 2.6 | 14 |
| 106 | Zincblendeâ€toâ€wurtzite interface improvement by group III loading in Auâ€seeded GaAs nanowires. Physica Status Solidi - Rapid Research Letters, 2013, 7, 855-859. | 2.4 | 13 |
| 107 | Phonon Transport and Thermoelectricity in Defect-Engineered InAs Nanowires. Materials Research Society Symposia Proceedings, 2012, 1404, 36. | 0.1 | 6 |
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| 111 | Demonstration of Defect-Free and Composition Tunable Ga<sub><i>x</i></sub>In<sub>1â€“<i>x</i></sub>Sb Nanowires. Nano Letters, 2012, 12, 4914-4919. | 9.1 | 44 |
| 112 | High-Performance InAs Nanowire MOSFETs. IEEE Electron Device Letters, 2012, 33, 791-793. | 3.9 | 60 |
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| 114 | Growth of InAs/InP coreâ€“shell nanowires with various pure crystal structures. Nanotechnology, 2012, 23, 285601. | 2.6 | 50 |
| 115 | Uniform and position-controlled InAs nanowires on 2â€²â€²Si substrates for transistor applications. Nanotechnology, 2012, 23, 015302. | 2.6 | 36 |
| 116 | Carrier control and transport modulation in GaSb/InAsSb core/shell nanowires. Applied Physics Letters, 2012, 101, . | 3.3 | 43 |
| 117 | Controlling the Abruptness of Axial Heterojunctions in IIIâ€“V Nanowires: Beyond the Reservoir Effect. Nano Letters, 2012, 12, 3200-3206. | 9.1 | 121 |
| 118 | Electrical properties of InAs1âˆ’xSbx and InSb nanowires grown by molecular beam epitaxy. Applied Physics Letters, 2012, 100, 232105. | 3.3 | 56 |
| 119 | Highly controlled InAs nanowires on Si(111) wafers by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 206-209. | 0.8 | 17 |
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| 121 | Simultaneous growth mechanisms for Cu-seeded InP nanowires. Nano Research, 2012, 5, 297-306. | 10.4 | 25 |
| 122 | High crystal quality wurtzite-zinc blende heterostructures in metal-organic vapor phase epitaxy-grown GaAs nanowires. Nano Research, 2012, 5, 470-476. | 10.4 | 51 |
| 123 | Crystal structure control in Au-free self-seeded InSb wire growth. Nanotechnology, 2011, 22, 145603. | 2.6 | 45 |
| 124 | Recent advances in semiconductor nanowire heterostructures. CrystEngComm, 2011, 13, 7175. | 2.6 | 104 |
| 125 | Thermal conductivity of indium arsenide nanowires with wurtzite and zinc blende phases. Physical Review B, 2011, 83, . | 3.2 | 96 |
| 126 | Formation of the Axial Heterojunction in GaSb/InAs(Sb) Nanowires with High Crystal Quality. Crystal Growth and Design, 2011, 11, 4588-4593. | 3.0 | 35 |

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| 128 | High Current Density Esaki Tunnel Diodes Based on GaSb-InAsSb Heterostructure Nanowires. Nano Letters, 2011, 11, 4222-4226. | 9.1 | 106 |
| 129 | High quality InAs and GaSb thin layers grown on Si (111). Journal of Crystal Growth, 2011, 332, 12-16. | 1.5 | 54 |
| 130 | Effects of Crystal Phase Mixing on the Electrical Properties of InAs Nanowires. Nano Letters, 2011, 11, 2424-2429. | 9.1 | 211 |
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| 134 | Parameter space mapping of InAs nanowire crystal structure. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 04D103. | 1.2 | 43 |
| 135 | Enhanced Sb incorporation in InAsSb nanowires grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2011, 98, . | 3.3 | 56 |
| 136 | Diameter reduction of nanowire tunnel heterojunctions using in situ annealing. Applied Physics Letters, 2011, 99, 203101. | 3.3 | 13 |
| 137 | A comparative study of the effect of gold seed particle preparation method on nanowire growth. Nano Research, 2010, 3, 506-519. | 10.4 | 43 |
| 138 | Control of IIIâ€"V nanowire crystal structure by growth parameter tuning. Semiconductor Science and Technology, 2010, 25, 024009. | 2.0 | 219 |
| 139 | Gold-free GaAs/GaAsSb heterostructure nanowires grown on silicon. Applied Physics Letters, 2010, 96, . | 3.3 | 83 |
| 140 | Branched nanotrees with immobilized acetylcholine esterase for nanobiosensor applications. Nanotechnology, 2010, 21, 055102. | 2.6 | 10 |
| 141 | Crystal Phase Engineering in Single InAs Nanowires. Nano Letters, 2010, 10, 3494-3499. | 9.1 | 234 |
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| 154 | GaAs/GaSb nanowire heterostructures grown by MOVPE. Journal of Crystal Growth, 2008, 310, 4115-4121. | 1.5 | 85 |
| 155 | Characterization of GaSb nanowires grown by MOVPE. Journal of Crystal Growth, 2008, 310, 5119-5122. | 1.5 | 45 |
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| 159 | Precursor evaluation for<i>in situ</i>InP nanowire doping. Nanotechnology, 2008, 19, 445602. | 2.6 | 92 |
| 160 | Control of GaP and GaAs Nanowire Morphology through Particle and Substrate Chemical Modification. Nano Letters, 2008, 8, 4087-4091. | 9.1 | 35 |
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